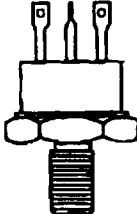


NEW ENGLAND SEMICONDUCTOR

POWER MOSFETS P CHANNEL

PACKAGE	DEVICE TYPE	BV_{DSS} VOLTS	I_D AMPS	$R_{DS(on)}$ @0.5 I_D OHMS	Q_g nc	C_{ISS} pf	P_D WATTS
TO-254 	NSFM9140	-100	-15.0	0.21	55	1200 *	96
	NSFM9240	-200	-9.3	0.51	57	1400 *	96
TO-257 	NSFY9130	-100	-5.3	0.6	45	700	45
	NSFY9140	-100	-9.3	0.31	55	1200	50
TO-61 ISOLATED 	NSF82208	-200	-6.5	0.8	45	650	75
	NSF82103	-100	-12.0	0.3	45	700	75
LCC-3 CERAMIC CHIP CARRIER 	NSLC9130	100	12.0	0.3	45	700 *	
	NSLC9230	200	6.5	0.8	55	1200 *	
	NSLC9140	100	19.0	0.2	55	1200 *	
	NSLC9240	200	11.0	0.5	57	1400 *	
PACKAGE	DEVICE TYPE	BV_{DSS} VOLTS	I_D AMPS	$R_{DS(on)}$ @0.5 I_D OHMS	$V_{GS(th)}$ min/max VOLTS	C_{ISS} pf	P_D WATTS
14 PIN QUAD DUAL IN LINE 	NFQ2000	-60	-0.24	10.0	-1/-3	50	1.3
	NFQ2001	-30	-0.6	2.0	-2/-4.5	150	1.3
	NFQ2004	-60	-0.41	5.0	-2/-4.5	150	1.3
	NFQ2006	-90	-0.41	5.0	-2/-4.5	150	1.3

- Electrical Characteristics @ 25° C unless otherwise noted
- Operational Temperature range: -55° to +150° C
- Storage temperature range: -55° to +150° C
- * Typical Value